

GDE25-1

Description:

Triad gate drive transformers are used universally in all high frequency switching topologies to isolate the control circuitry from the line-connected switches. The Windings are interleaved for the lowest possible leakage inductance. Turn ratios optimize coupling and enhance performance. Available with single or dual secondaries, these transformers are constructed of UL rated 130° materials and are easily standardized at operating frequencies of 200 kHz and beyond.

Electrical Specifications (@25C):

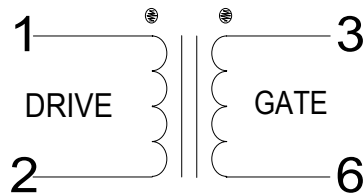
Max DCR 1-2	Max DCR Gate	Min. ET Product	Max. Leakage	Min. Inductance	Turns Ratio
.350 Ω	.350 Ω	540 VμSec	2.5 μH	.680 mH	1:1

Weight: .045 oz.

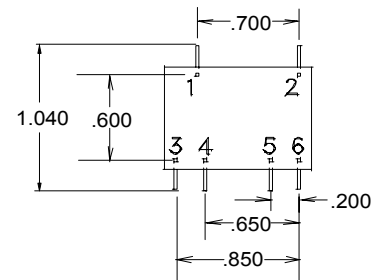
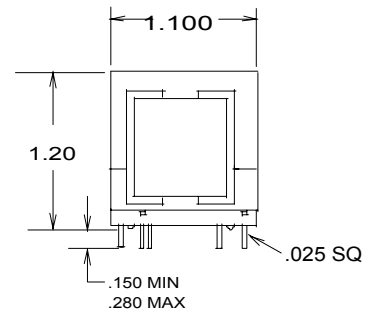
Technical Notes:

1. Drive to gate winding hi-pot tested at 3,750 VRMS.
2. Derate ET product by 32% for 50 kHz, 50% for 100 kHz and for unidirectional operation.
3. Operation at rated current per winding renders approximately 40° temperature rise.

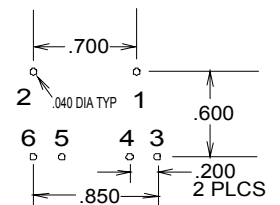
Schematic:



RoHS Compliance: As of manufacturing date February 2005, all standard products meet the requirements of 2002/95/EC, known as the RoHS initiative.



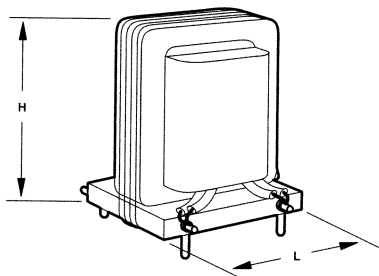
BOTTOM VIEW



MOUNTING HOLE PATTERN TOP VIEW

Switchmode/High Frequency

Gate Drive Transformers



:: Description

Triad gate drive transformers are used universally in all high frequency switching topologies to isolate the control circuitry from the line-connected switches. The windings are interleaved for the lowest possible practical leakage inductance. Turn ratios of 1:1 and 1:1.5 optimize coupling and enhance performance. Available with single or dual secondaries, these transformers constructed of UL rated 130°C materials are easily standardized at operating frequencies 200 kHz and beyond.

:: Gate Drive Transformers

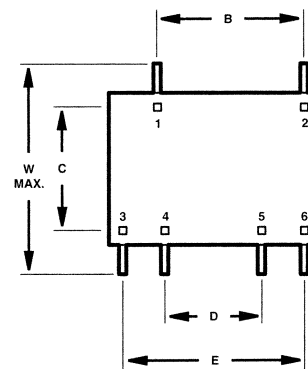
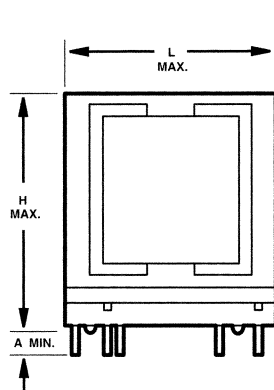
Section	Type No.	Max. DCR 1-2	Max. DCR Gate	Min. ET Product	Max. Leakage	Min. Inductance	Turns Ratio	Dimensions							Wt. Oz.	
								H	W	L	A	B	C	D		E
A	GDE25-1	.350 Ohms	.350 Ohms	540 VpSec	2.5 µH	.680 mH	1:1	1.20	1.04	1.10	.150	.700	.600	.450	.850	.045
	GDE25-2	.350 Ohms	.650 Ohms	540 VpSec	2.5 µH	.680 mH	1:1:1									
	GDE25-3	.875 Ohms	.350 Ohms	840 VpSec	3.5 µH	1.50 mH	1:5:1									
	GDE25-4	.875 Ohms	.650 Ohms	840 VpSec	3.5 µH	1.50 mH	1.5:1:1									
	GDE25-5	.350 Ohms	.875 Ohms	540 VpSec	3.5 µH	.680 mH	1:1.5									
	GDE25-6	.350 Ohms	1.75 Ohms	540 VpSec	3.5 µH	.680 mH	1:1.5:1.5									

A GDE25 KIT is available which includes one of each of the above listed components.

:: Outline Dimensions

Technical Notes

1. Drive to gate winding hi-pot tested at 3,750 VRMS.
2. Derate ET product by 32% for 50 kHz, 50% for 100 kHz and 50% for unidirectional operation.
3. Operation at rated current per winding renders approximately 40°C temperature rise.



bottom view

